BCE化可能な酸化物半導体材料

BCEプロセスへ適用可能な酸化物半導体TFT用ターゲット
Oxide Semiconductor Sputtering Targets which are applicable to BCE Process for Thin Film Transistor

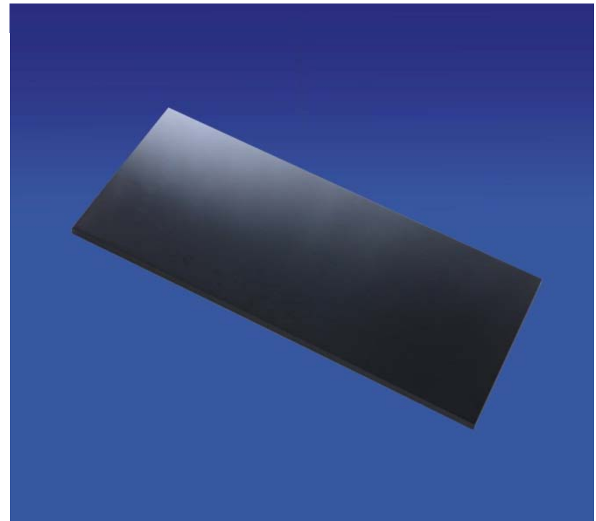
■KOS-B02　Features

・Resistant to PAN etchant
　⇨ Applicable to BCE process

・Applicable to the same processes of forming IGZO

■KOS-B02 sputtering target characteristics

Density	≧98%
Resistivity	1～3 x 10^{-2} Ω・cm
Purity	4N

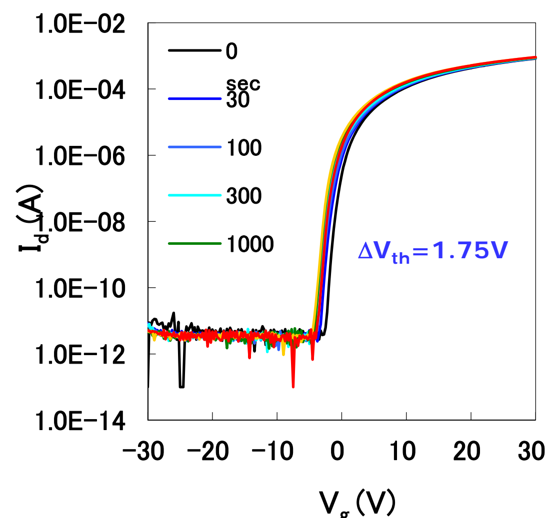


■KOS-B02 film characteristics（BCE-TYPE）

Mobility	5 ～ 15 cm^2/Vs

	Etching rate (nm/min.)
KOS-B02	0
IGZO	66

Etchant: PAN for Mo/Al/Mo
Mixed acid (H_3PO_4, HNO_3, CH_3COOH)



Measurement condition:
Vg= -20V, Vd= 10V, 60°C,
White LED (25000nit), 2hrs,
Exposure from the bottom side of TFT